



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

MPS2222

TRANSISTOR (NPN)

FEATURE

Power dissipation

P_{CM} : 0.625 W ($T_{amb}=25^{\circ}C$)

Collector current

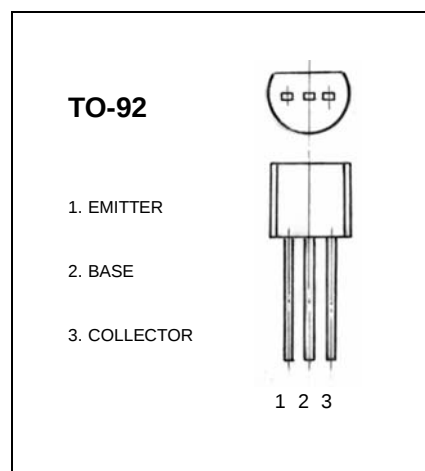
I_{CM} : 0.6 A

Collector-base voltage

$V_{(BR)CBO}$: 60 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10mA, I_B = 0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 50V, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 3V, I_C = 0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 10V, I_C = 150mA$	100		300	
	$h_{FE(2)}$	$V_{CE} = 10V, I_C = 1mA$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500mA, I_B = 50mA$			1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500mA, I_B = 50mA$			2	V
Transition frequency	f_T	$V_{CE} = 20V, I_C = 20mA$ $f = 100MHz$	300			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H
Range	100-200	200-300